TOSHIBA

MICROWAVE SEMICONDUCTOR

TECHNICAL DATA

MICROWAVE POWER MMIC AMPLIFIER

TMD0608-4

FEATURES

- **HIGH POWER**
  P1dB=36.0dBm at 5.65GHz to 8.50GHz
- **HIGH GAIN**
  G1dB=28.0dB at 5.65GHz to 8.50GHz
- **BROAD BAND INTERNALLY MATCHED**
- **HERMETICALLY SEALED PACKAGE**

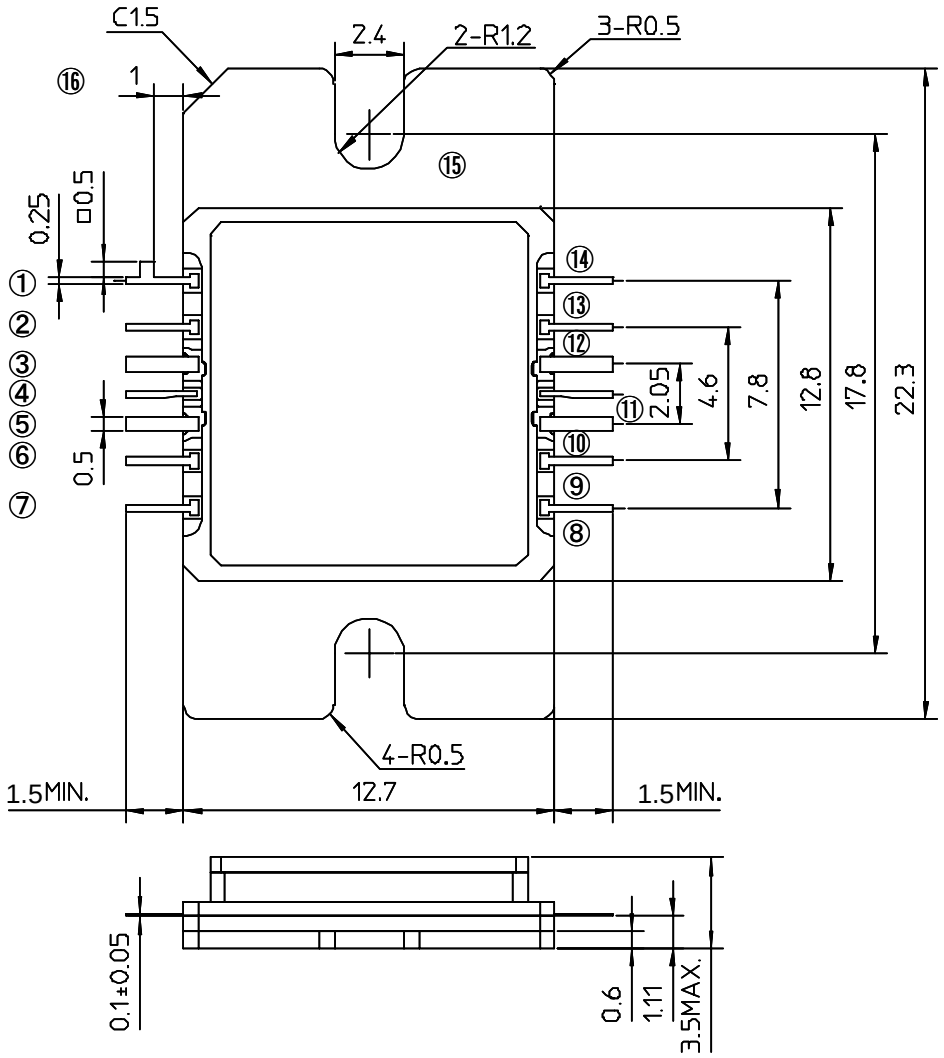
ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain Supply Voltage	V_{DD}	V	15
Gate Supply Voltage	V_{GG}	V	-5
Input Power	P_{in}	dBm	18
Flange Temperature	T_c	°C	-30 to +80
Storage Temperature	T_{stg}	°C	-65 to +175

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P_{1dB}	V_{DD}= 10V IDDset= 1.9A f = 5.65 to 8.50GHz	dBm	34.5	36.0	—
Power Gain at 1dB Gain Compression Point	G_{1dB}		dB	25.0	28.0	—
Drain Current	I_{DD}		A	—	2.6	3.0
3rd Order Intermodulation Distortion	IM3	Two-tone test Po=25.5dBm (single carrier level)	dBc	-37	-40	—

PACKAGE OUTLINE (7-BA25A)



①VGG ②N.C. ③GND ④RFin ⑤GND ⑥N.C ⑦VGG

⑧VDD ⑨N.C ⑩GND ⑪RFout ⑫GND ⑬N.C. ⑭VDD

⑮GND ⑯Pin #1 tab

Unit: mm